



**Tokyo Electron Ltd. Trias Ti/TiN
Metal CVD (Chemical Vapor Deposition)**

**Currently Configured for 300mm wafer size
MFG Date: February 10, 2009**

EQUIPMENT DETAILS:

[PM1]

Process: TiN

Hard: SFD

**Gas(sccm): TiCl4(100), ClF3(500), N2(600/2000), NH3(5000), NH3(300), N2(600/2000),
NH3(1000), N2(300)**

[PM2]

Process: Ti

Hard: HT

**Gas(sccm): TiCl4(20), ClF3(500), Ar(2000), H2(5000), NH3(600/2000), N2(2000), Ar(300)
RF: 450kHz/2000W**

[PM3]

Process: TiN

Hard: SFD

**Gas(sccm): TiCl4(100), ClF3(500), N2(600/2000), NH3(5000), NH3(300), N2(600/2000),
NH3(1000), N2(300)**

[PM4]

Process: Ti

Hard: HP

**Gas(sccm): TiCl4(20), ClF3(500), Ar(2000), H2(5000), NH3(600/2000), N2(2000), Ar(300)
RF: 450kHz/2000W**

No missing or damaged parts.